

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

Dual Bias Resistor Transistors

NPN Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the MUN5211DW1T1G series, two BRT devices are housed in the SOT-363 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- AEC-Q101 Qualified and PPAP Capable
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

(T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current	I _C	100	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

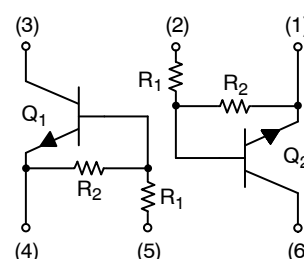


ON Semiconductor®

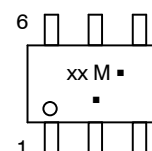
<http://onsemi.com>



SOT-363
CASE 419B
STYLE 1



MARKING DIAGRAM



xx = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or position may vary depending upon manufacturing location.

DEVICE MARKING INFORMATION

See specific marking information in the device marking table on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

THERMAL CHARACTERISTICS

Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	187 (Note 1) 256 (Note 2) 1.5 (Note 1) 2.0 (Note 2)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	670 (Note 1) 490 (Note 2)	$^\circ\text{C/W}$
Characteristic (Both Junctions Heated)	Symbol	Max	Unit
Total Device Dissipation $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	250 (Note 1) 385 (Note 2) 2.0 (Note 1) 3.0 (Note 2)	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	493 (Note 1) 325 (Note 2)	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Lead	$R_{\theta JL}$	188 (Note 1) 208 (Note 2)	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

- FR-4 @ Minimum Pad
- FR-4 @ 1.0 x 1.0 inch Pad

DEVICE MARKING AND RESISTOR VALUES

Device	Package	Marking	R1 (K)	R2 (K)	Shipping [†]
MUN5211DW1T1G, SMUN5211DW1T1G	SOT-363 (Pb-Free)	7A	10	10	3,000 / Tape & Reel
MUN5212DW1T1G, NSVMUN5212DW1T1G	SOT-363 (Pb-Free)	7B	22	22	3,000 / Tape & Reel
MUN5213DW1T1G, SMUN5213DW1T1G	SOT-363 (Pb-Free)	7C	47	47	3,000 / Tape & Reel
MUN5214DW1T1G, SMUN5214DW1T1G	SOT-363 (Pb-Free)	7D	10	47	3,000 / Tape & Reel
MUN5215DW1T1G	SOT-363 (Pb-Free)	7E	10	∞	3,000 / Tape & Reel
MUN5216DW1T1G, SMUN5216DW1T1G	SOT-363 (Pb-Free)	7F	4.7	∞	3,000 / Tape & Reel
MUN5230DW1T1G, SMUN5230DW1T1G	SOT-363 (Pb-Free)	7G	1.0	1.0	3,000 / Tape & Reel
MUN5231DW1T1G, SMUN5231DW1T1G	SOT-363 (Pb-Free)	7H	2.2	2.2	3,000 / Tape & Reel
MUN5232DW1T1G, SMUN5232DW1T1G	SOT-363 (Pb-Free)	7J	4.7	4.7	3,000 / Tape & Reel
MUN5233DW1T1G, SMUN5233DW1T1G	SOT-363 (Pb-Free)	7K	4.7	47	3,000 / Tape & Reel
MUN5234DW1T1G	SOT-363 (Pb-Free)	7L	22	47	3,000 / Tape & Reel
MUN5235DW1T1G, SMUN5235DW1T1G	SOT-363 (Pb-Free)	7M	2.2	47	3,000 / Tape & Reel
MUN5236DW1T1G	SOT-363 (Pb-Free)	7N	100	100	3,000 / Tape & Reel
MUN5237DW1T1G, SMUN5237DW1T1G	SOT-363 (Pb-Free)	7P	47	22	3,000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted, common for Q₁ and Q₂)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V _{CB} = 50 V, I _E = 0)	I _{CBO}	–	–	100	nAdc
Collector-Emitter Cutoff Current (V _{CE} = 50 V, I _B = 0)	I _{CEO}	–	–	500	nAdc
Emitter-Base Cutoff Current (V _{EB} = 6.0 V, I _C = 0)	I _{EBO}				mAdc
MUN5211DW1T1G, SMUN5211DW1T1G		–	–	0.5	
MUN5212DW1T1G, NSVMUN5212DW1T1G		–	–	0.2	
MUN5213DW1T1G, SMUN5213DW1T1G		–	–	0.1	
MUN5214DW1T1G, SMUN5214DW1T1G		–	–	0.2	
MUN5215DW1T1G		–	–	0.9	
MUN5216DW1T1G, SMUN5216DW1T1G		–	–	1.9	
MUN5230DW1T1G, SMUN5230DW1T1G		–	–	4.3	
MUN5231DW1T1G, SMUN5231DW1T1G		–	–	2.3	
MUN5232DW1T1G, SMUN5232DW1T1G		–	–	1.5	
MUN5233DW1T1G, SMUN5233DW1T1G		–	–	0.18	
MUN5234DW1T1G		–	–	0.13	
MUN5235DW1T1G, SMUN5235DW1T1G		–	–	0.2	
MUN5236DW1T1G		–	–	0.05	
MUN5237DW1T1G, SMUN5237DW1T1G		–	–	0.13	
Collector-Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	50	–	–	Vdc
Collector-Emitter Breakdown Voltage (Note 3) (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	–	–	Vdc

ON CHARACTERISTICS (Note 3)

DC Current Gain (V _{CE} = 10 V, I _C = 5.0 mA)	h _{FE}				
MUN5211DW1T1G, SMUN5211DW1T1G		35	60	–	
MUN5212DW1T1G, NSVMUN5212DW1T1G		60	100	–	
MUN5213DW1T1G, SMUN5213DW1T1G		80	140	–	
MUN5214DW1T1G, SMUN5214DW1T1G		80	140	–	
MUN5215DW1T1G		160	350	–	
MUN5216DW1T1G, SMUN5216DW1T1G		160	350	–	
MUN5230DW1T1G, SMUN5230DW1T1G		3.0	5.0	–	
MUN5231DW1T1G, SMUN5231DW1T1G		8.0	15	–	
MUN5232DW1T1G, SMUN5232DW1T1G		15	30	–	
MUN5233DW1T1G, SMUN5233DW1T1G		80	200	–	
MUN5234DW1T1G		80	150	–	
MUN5235DW1T1G, SMUN5235DW1T1G		80	140	–	
MUN5236DW1T1G		80	150	–	
MUN5237DW1T1G, SMUN5237DW1T1G		80	140	–	
Collector-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.3 mA)	V _{CE(sat)}				Vdc
MUN5211DW1T1G, SMUN5211DW1T1G		–	–	0.25	
MUN5212DW1T1G, NSVMUN5212DW1T1G		–	–	0.25	
MUN5213DW1T1G, SMUN5213DW1T1G		–	–	0.25	
MUN5214DW1T1G, SMUN5214DW1T1G		–	–	0.25	
MUN5235DW1T1G, SMUN5235DW1T1G		–	–	0.25	
MUN5236DW1T1G		–	–	0.25	
(I _C = 10 mA, I _B = 5 mA)					
MUN5230DW1T1G, SMUN5230DW1T1G		–	–	0.25	
MUN5231DW1T1G, SMUN5231DW1T1G		–	–	0.25	
MUN5237DW1T1G, SMUN5237DW1T1G		–	–	0.25	
(I _C = 10 mA, I _B = 1 mA)					
MUN5215DW1T1G		–	–	0.25	
MUN5216DW1T1G, SMUN5216DW1T1G		–	–	0.25	
MUN5232DW1T1G, SMUN5232DW1T1G		–	–	0.25	
MUN5233DW1T1G, SMUN5233DW1T1G		–	–	0.25	
MUN5234DW1T1G		–	–	0.25	

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

Characteristic	Symbol	Min	Typ	Max	Unit
ON CHARACTERISTICS (Note 3)					
Output Voltage (on) ($V_{CC} = 5.0\text{ V}$, $V_B = 2.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5211DW1T1G, SMUN5211DW1T1G MUN5212DW1T1G, NSVMUN5212DW1T1G MUN5214DW1T1G, SMUN5214DW1T1G MUN5215DW1T1G MUN5216DW1T1G, SMUN5216DW1T1G MUN5230DW1T1G, SMUN5230DW1T1G MUN5231DW1T1G, SMUN5231DW1T1G MUN5232DW1T1G, SMUN5232DW1T1G MUN5233DW1T1G, SMUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G, SMUN5235DW1T1G ($V_{CC} = 5.0\text{ V}$, $V_B = 3.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5213DW1T1G, SMUN5213DW1T1G ($V_{CC} = 5.0\text{ V}$, $V_B = 5.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5236DW1T1G ($V_{CC} = 5.0\text{ V}$, $V_B = 4.0\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5237DW1T1G, SMUN5237DW1T1G	V_{OL}	–	–	0.2	Vdc
Output Voltage (off) ($V_{CC} = 5.0\text{ V}$, $V_B = 0.5\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5211DW1T1G, SMUN5211DW1T1G MUN5212DW1T1G, NSVMUN5212DW1T1G MUN5213DW1T1G, SMUN5213DW1T1G MUN5214DW1T1G, SMUN5214DW1T1G MUN5233DW1T1G, SMUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G, SMUN5235DW1T1G ($V_{CC} = 5.0\text{ V}$, $V_B = 0.050\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5230DW1T1G, SMUN5230DW1T1G ($V_{CC} = 5.0\text{ V}$, $V_B = 0.25\text{ V}$, $R_L = 1.0\text{ k}\Omega$) MUN5215DW1T1G MUN5216DW1T1G, SMUN5216DW1T1G MUN5231DW1T1G, SMUN5231DW1T1G MUN5232DW1T1G, SMUN5232DW1T1G MUN5236DW1T1G MUN5237DW1T1G, SMUN5237DW1T1G	V_{OH}	4.9	–	–	Vdc
Input Resistor MUN5211DW1T1G, SMUN5211DW1T1G MUN5212DW1T1G, NSVMUN5212DW1T1G MUN5213DW1T1G, SMUN5213DW1T1G MUN5214DW1T1G, SMUN5214DW1T1G MUN5215DW1T1G MUN5216DW1T1G, SMUN5216DW1T1G MUN5230DW1T1G, SMUN5230DW1T1G MUN5231DW1T1G, SMUN5231DW1T1G MUN5232DW1T1G, SMUN5232DW1T1G MUN5233DW1T1G, SMUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G, SMUN5235DW1T1G MUN5236DW1T1G MUN5237DW1T1G, SMUN5237DW1T1G	R1	7.0 15.4 32.9 7.0 7.0 3.3 0.7 1.5 3.3 3.3 15.4 1.54 70 32.9	10 22 47 10 10 4.7 1.0 2.2 4.7 4.7 22 2.2 100 47	13 28.6 61.1 13 13 6.1 1.3 2.9 6.1 6.1 28.6 2.86 130 61.1	k Ω
Resistor Ratio MUN5211DW1T1G/SMUN5211DW1T1G/MUN5212DW1T1G/ NSVMUN5212DW1T1G/MUN5213DW1T1G/SMUN5213DW1T1G/ MUN5236DW1T1G MUN5214DW1T1G/SMUN5214DW1T1G MUN5215DW1T1G/MUN5216DW1T1G/SMUN5216DW1T1G MUN5230DW/SMUN5230DW/MUN5231DW/SMUN5231DW MUN5232DW1T1G/SMUN5232DW1T1G MUN5233DW1T1G/SMUN5233DW1T1G MUN5234DW1T1G MUN5235DW1T1G/SMUN5235DW1T1G MUN5237DW1T1G/SMUN5237DW1T1G	R1/R2	0.8 0.17 – 0.8 0.055 0.38 0.038 1.7	1.0 0.21 – 1.0 0.1 0.47 0.047 2.1	1.2 0.25 – 1.2 0.185 0.56 0.056 2.6	

3. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

ALL MUN5211DW1T1G SERIES DEVICES

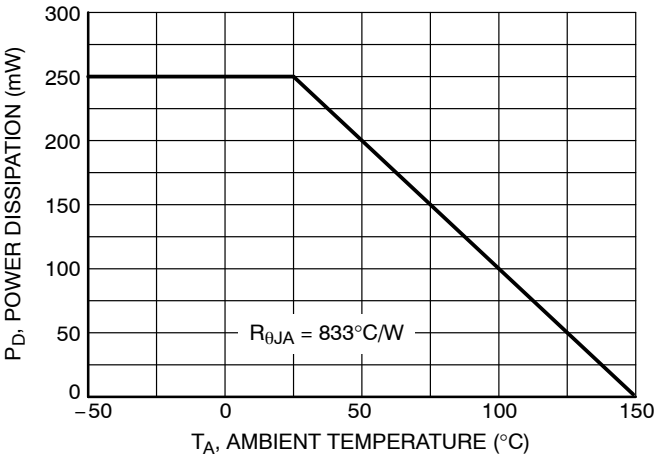


Figure 1. Derating Curve

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5211DW1T1G, SMUN5211DW1T1G

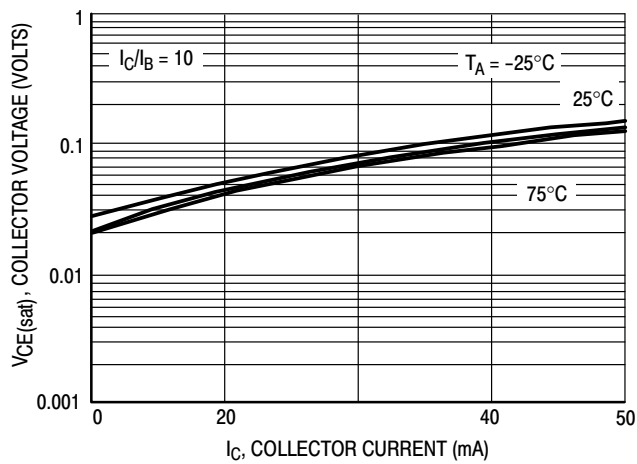


Figure 2. $V_{CE(sat)}$ versus I_C

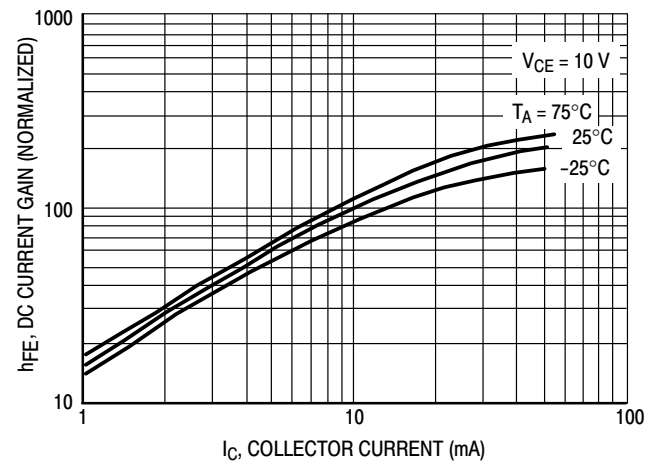


Figure 3. DC Current Gain

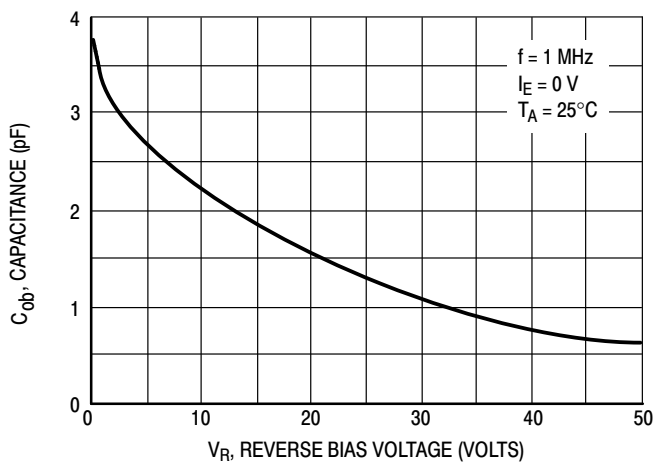


Figure 4. Output Capacitance

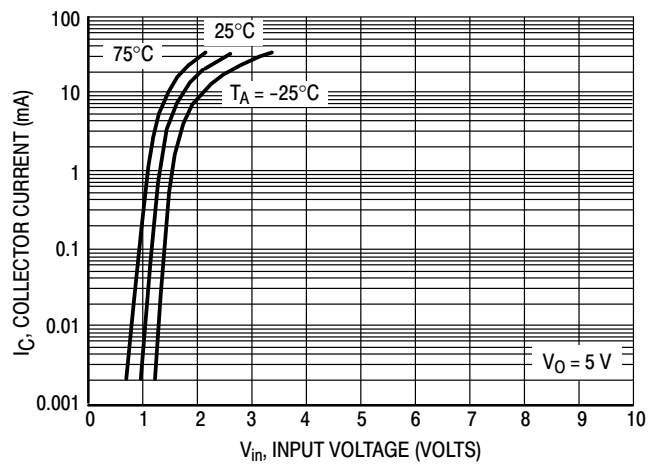


Figure 5. Output Current versus Input Voltage

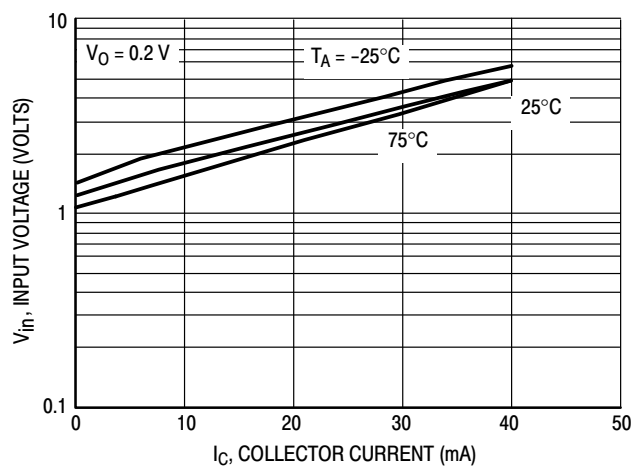


Figure 6. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5212DW1T1G, NSVMUN5212DW1T1G

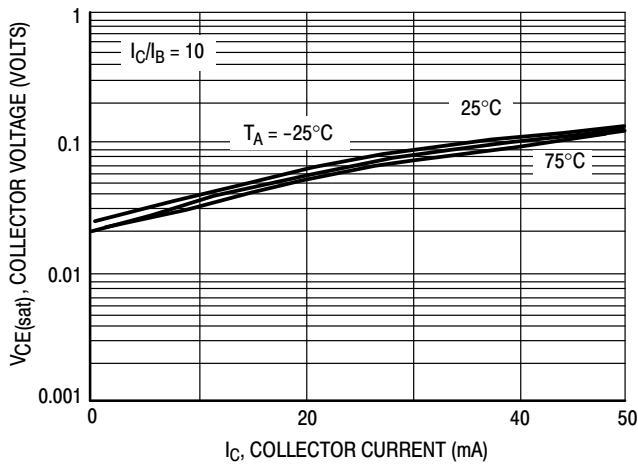


Figure 7. $V_{CE(sat)}$ versus I_C

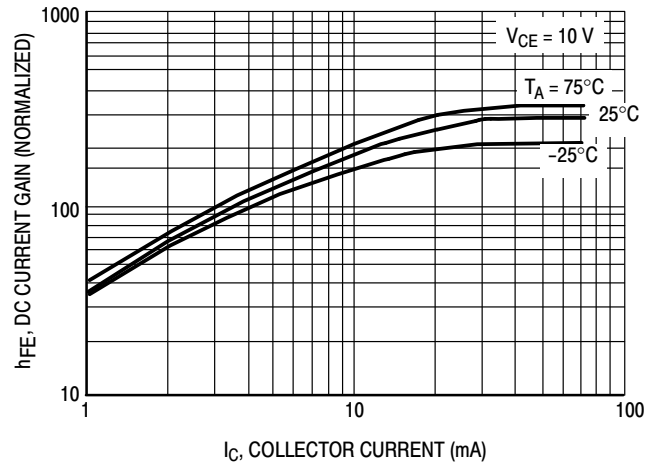


Figure 8. DC Current Gain

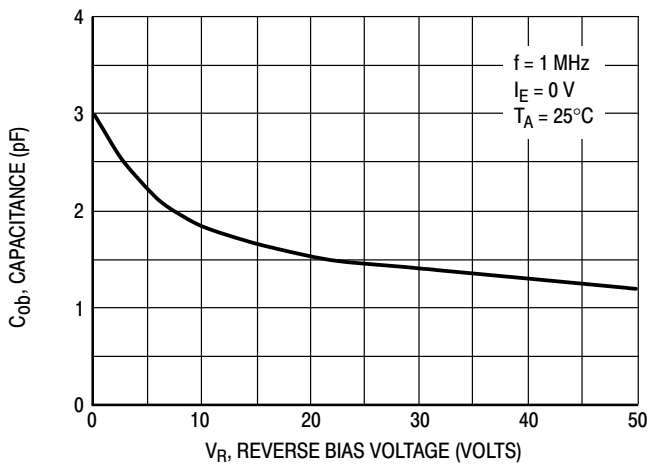


Figure 9. Output Capacitance

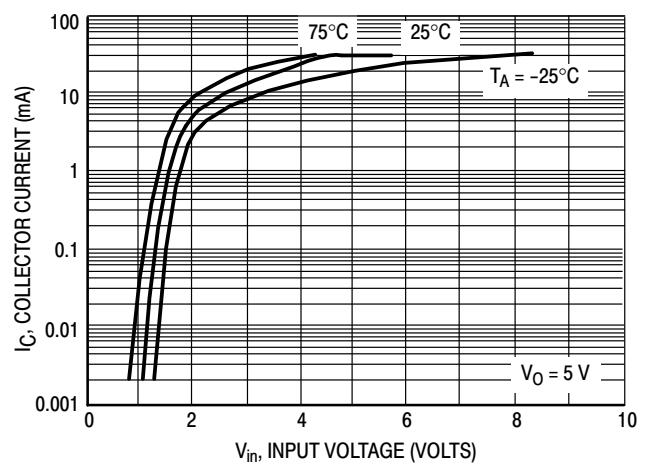


Figure 10. Output Current versus Input Voltage

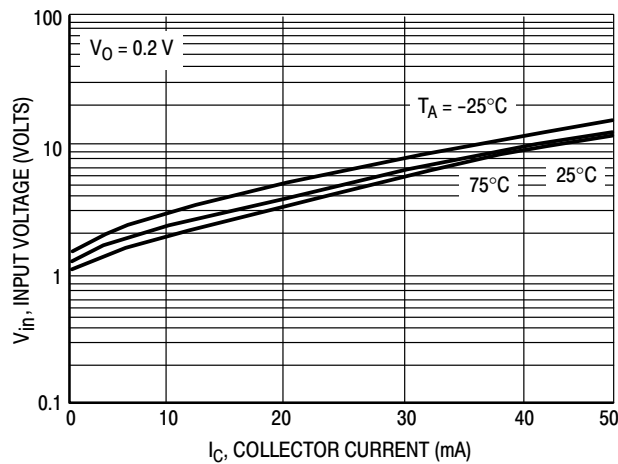


Figure 11. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5213DW1T1G, SMUN5213DW1T1G

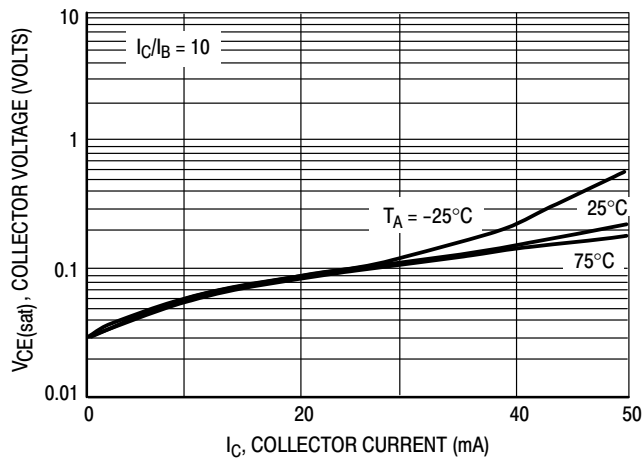


Figure 12. $V_{CE(sat)}$ versus I_C

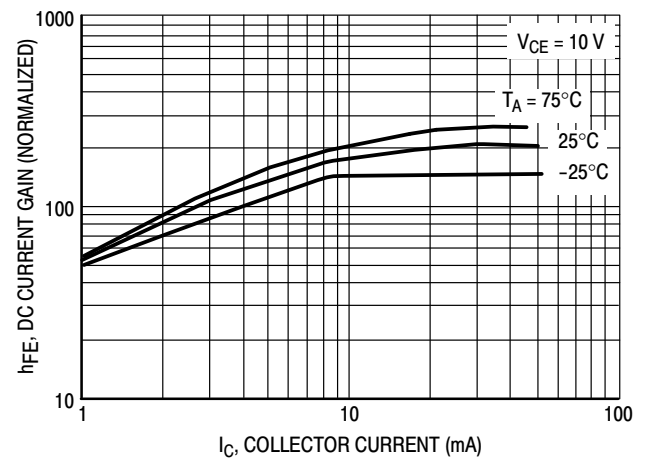


Figure 13. DC Current Gain

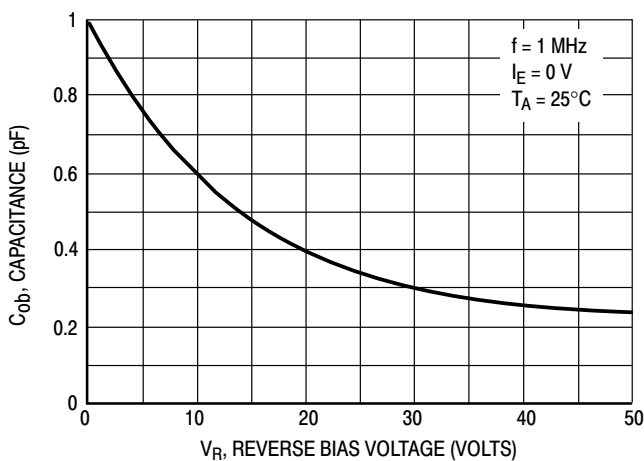


Figure 14. Output Capacitance

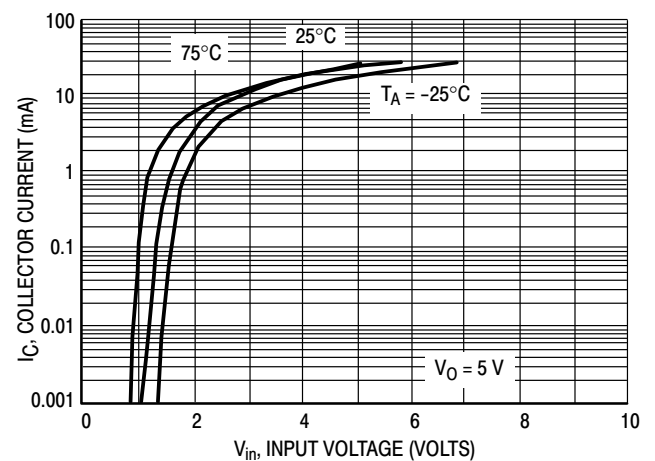


Figure 15. Output Current versus Input Voltage

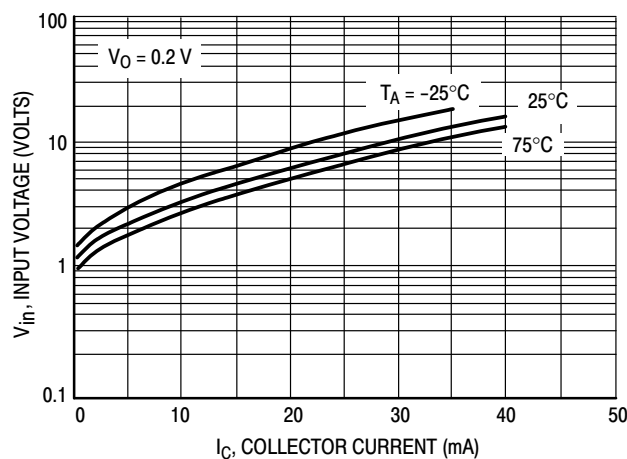


Figure 16. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5214DW1T1G, SMUN5214DW1T1G

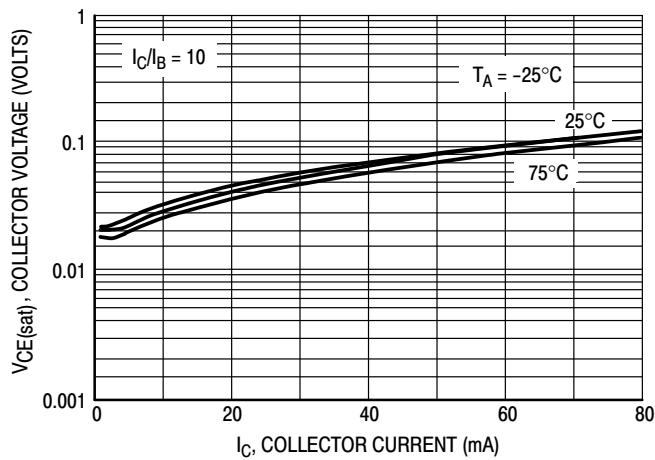


Figure 17. $V_{CE(sat)}$ versus I_C

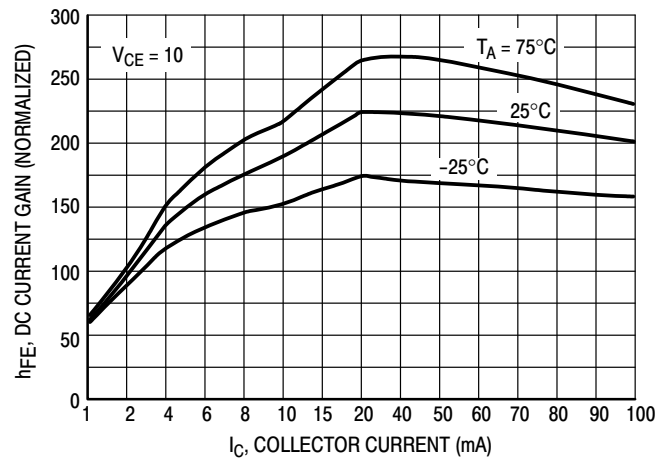


Figure 18. DC Current Gain

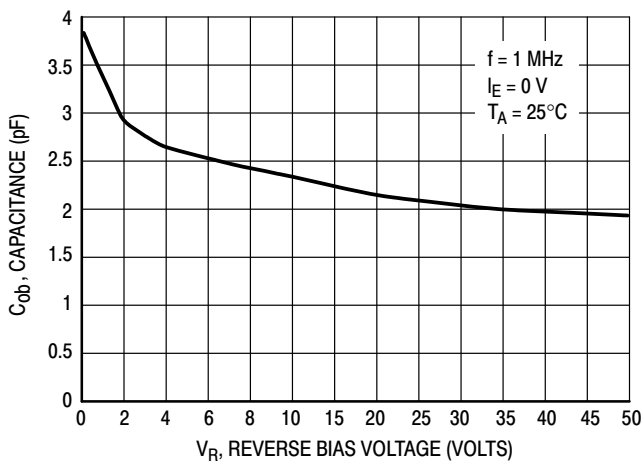


Figure 19. Output Capacitance

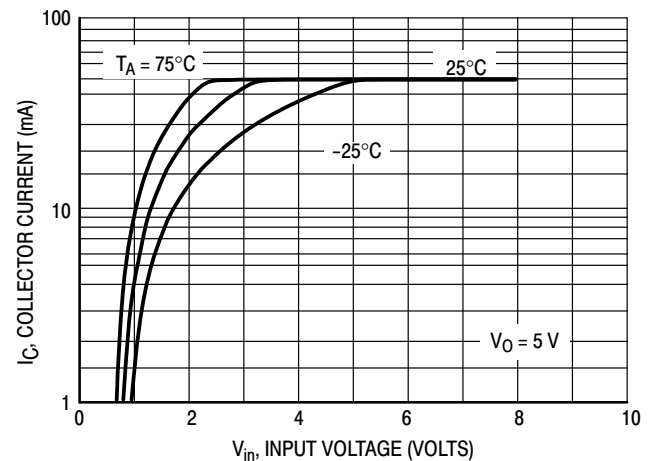


Figure 20. Output Current versus Input Voltage

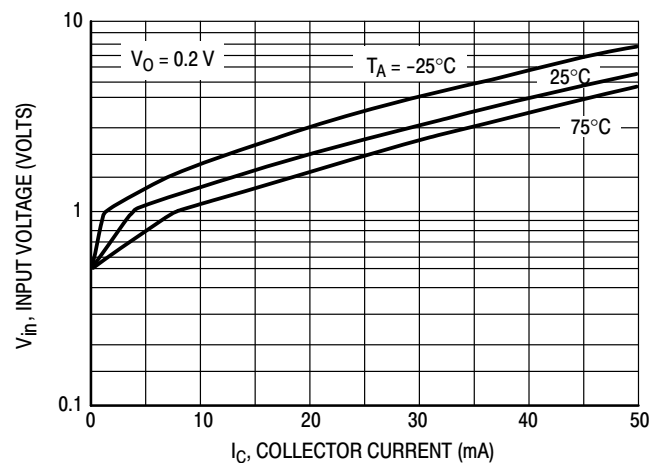


Figure 21. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5215DW1T1G

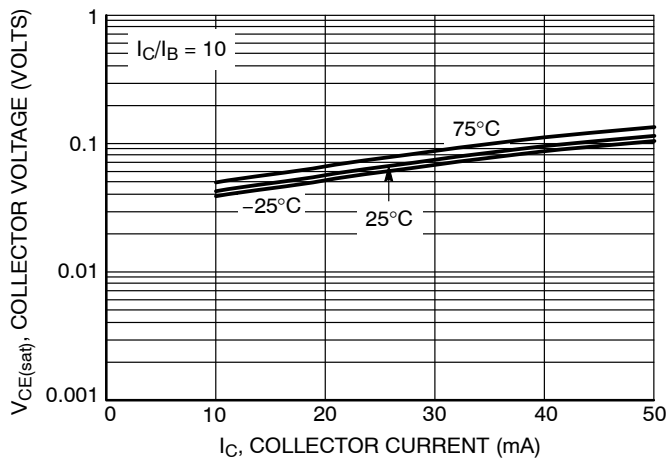


Figure 22. $V_{CE(sat)}$ versus I_C

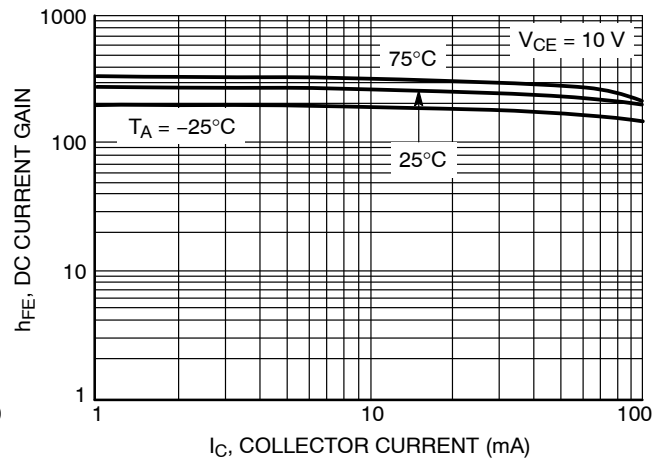


Figure 23. DC Current Gain

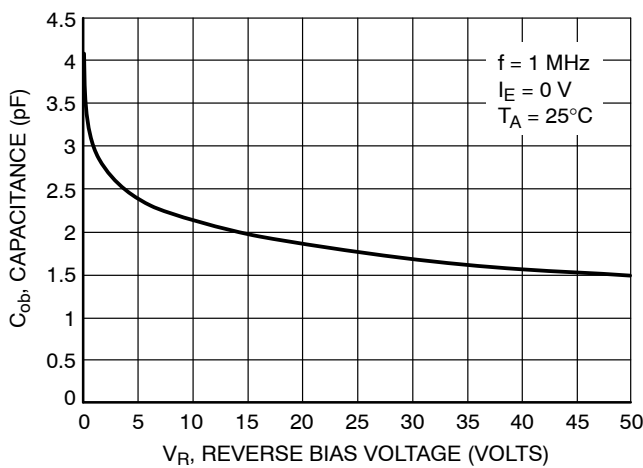


Figure 24. Output Capacitance

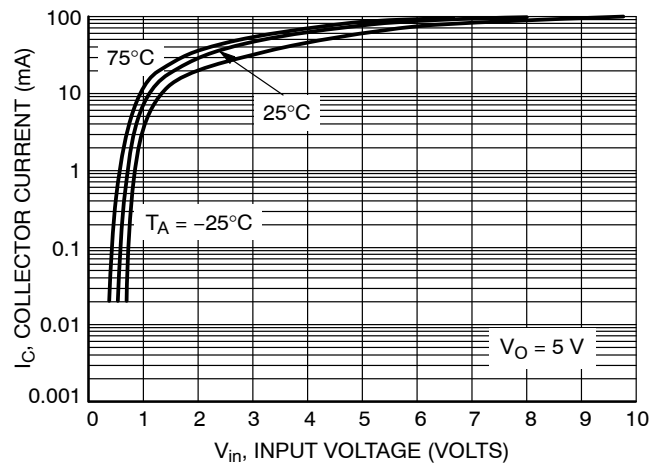


Figure 25. Output Current versus Input Voltage

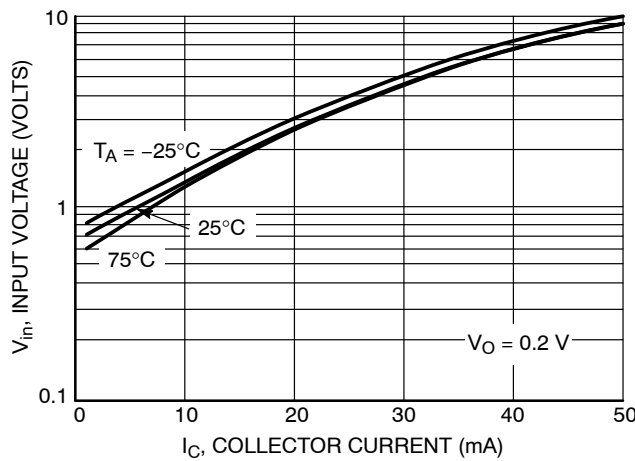


Figure 26. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5216DW1T1G, SMUN5216DW1T1G

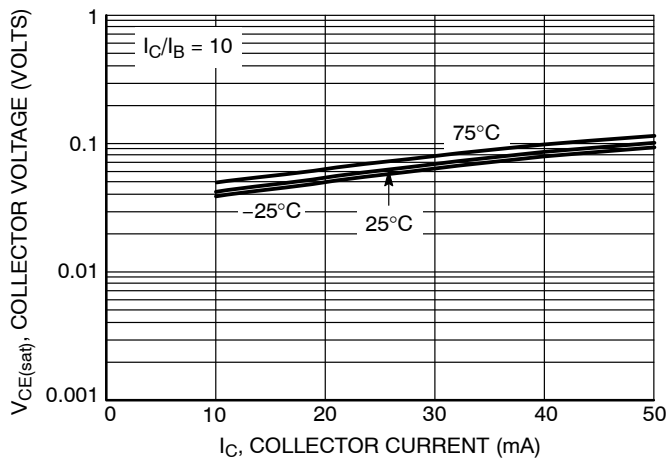


Figure 27. $V_{CE(sat)}$ versus I_C

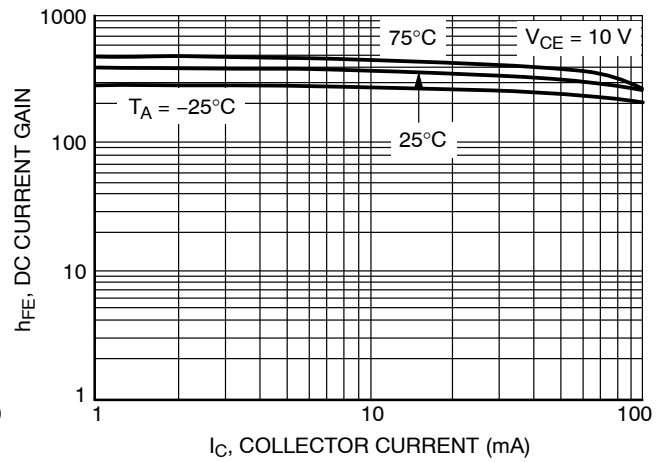


Figure 28. DC Current Gain

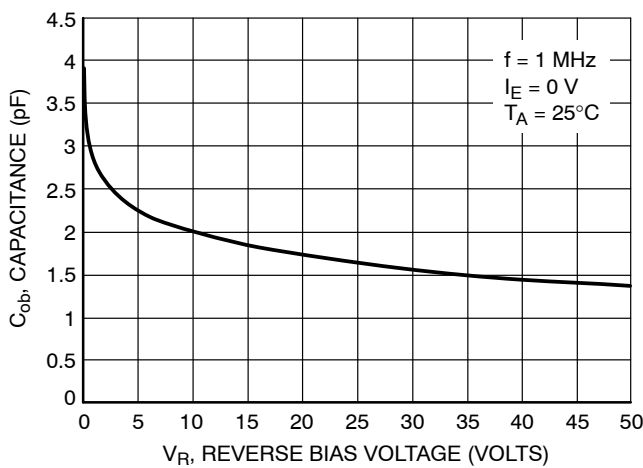


Figure 29. Output Capacitance

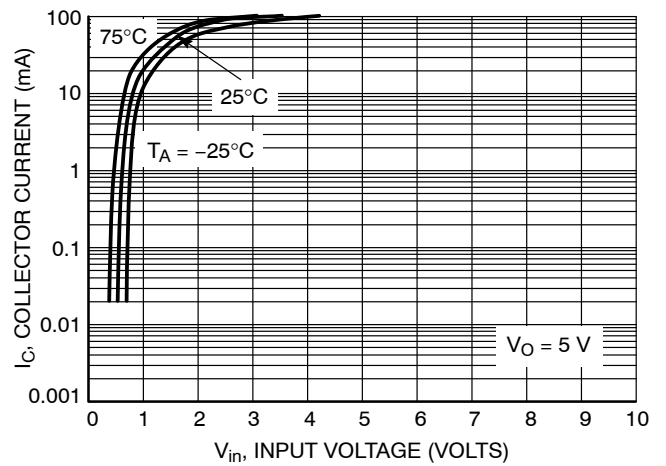


Figure 30. Output Current versus Input Voltage

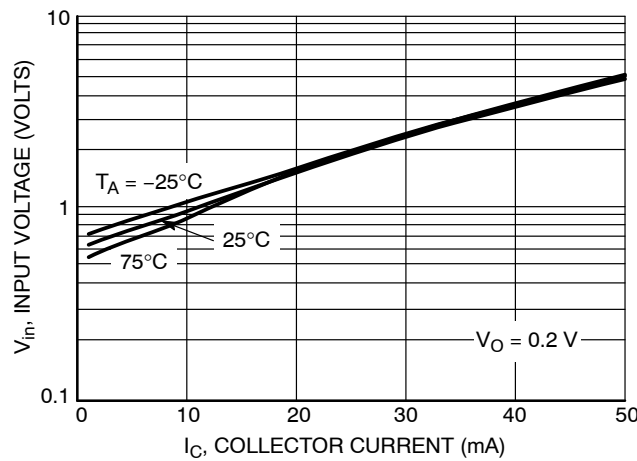


Figure 31. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5230DW1T1G, SMUN5230DW1T1G

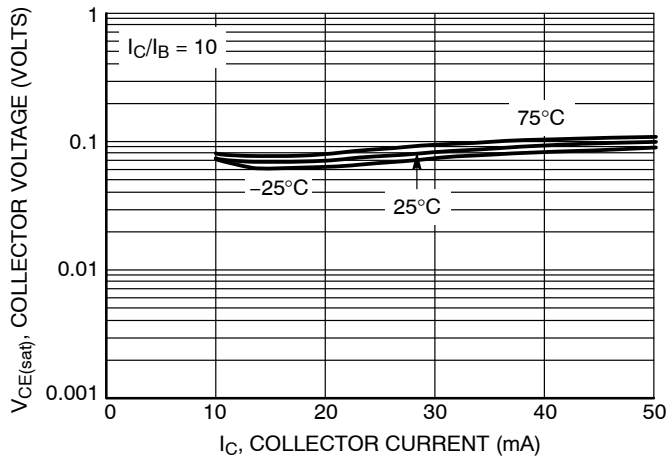


Figure 32. $V_{CE(sat)}$ versus I_C

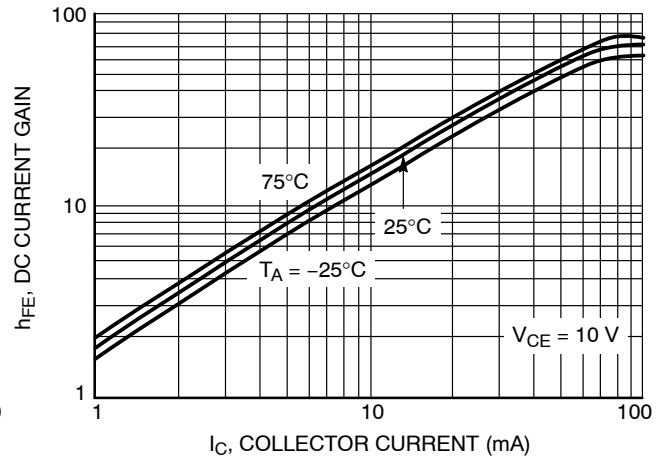


Figure 33. DC Current Gain

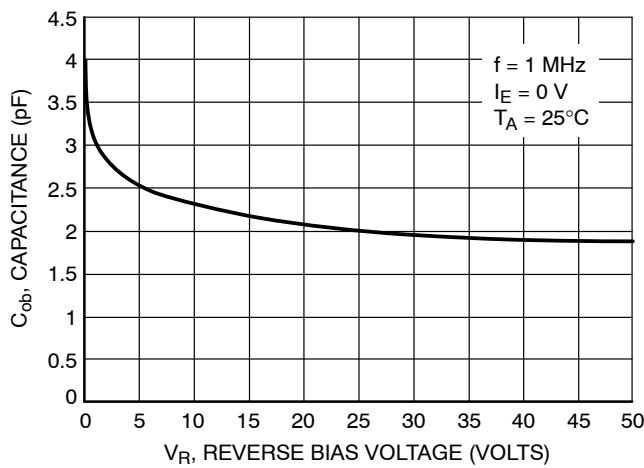


Figure 34. Output Capacitance

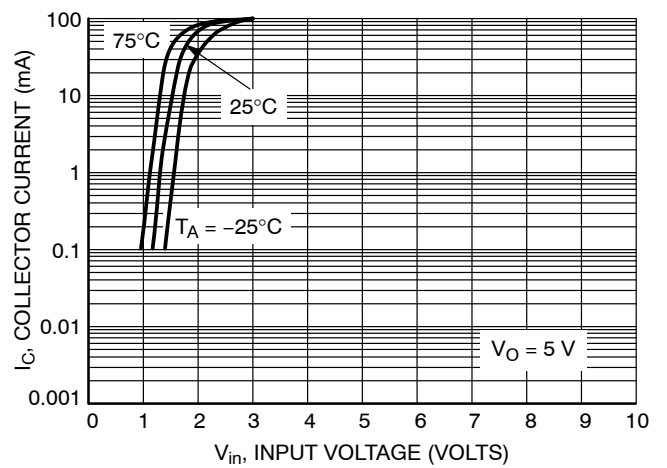


Figure 35. Output Current versus Input Voltage

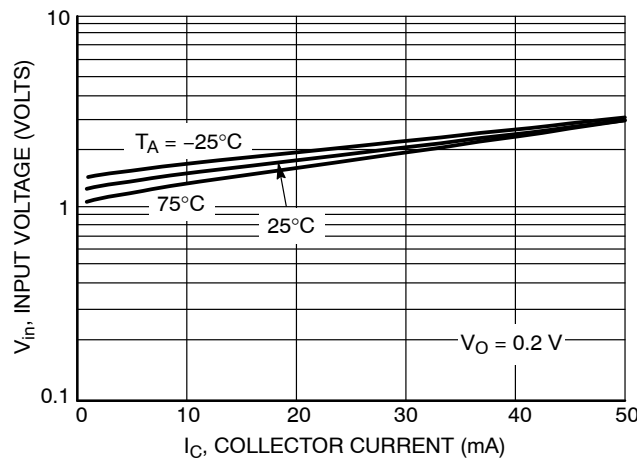


Figure 36. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5231DW1T1G, SMUN5231DW1T1G

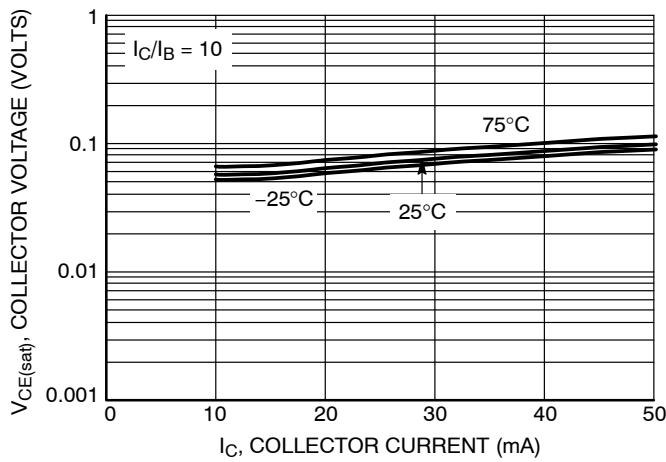


Figure 37. $V_{CE(sat)}$ versus I_C

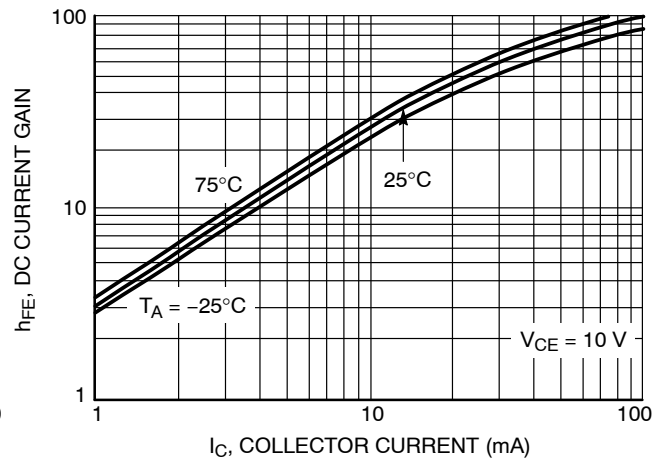


Figure 38. DC Current Gain

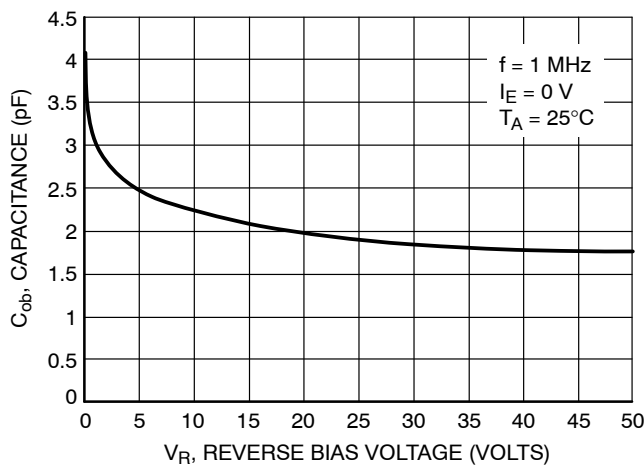


Figure 39. Output Capacitance

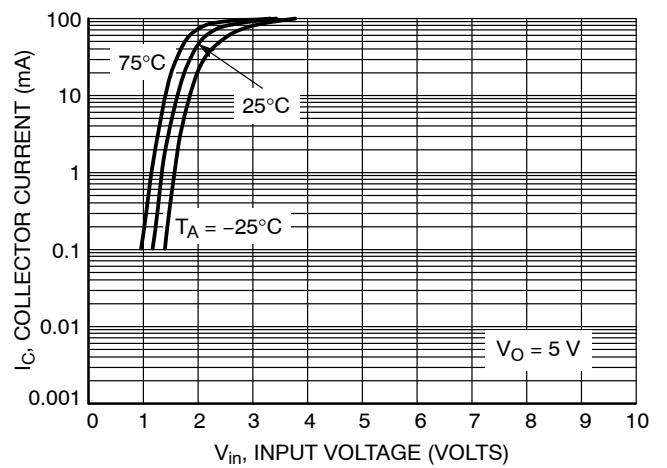


Figure 40. Output Current versus Input Voltage

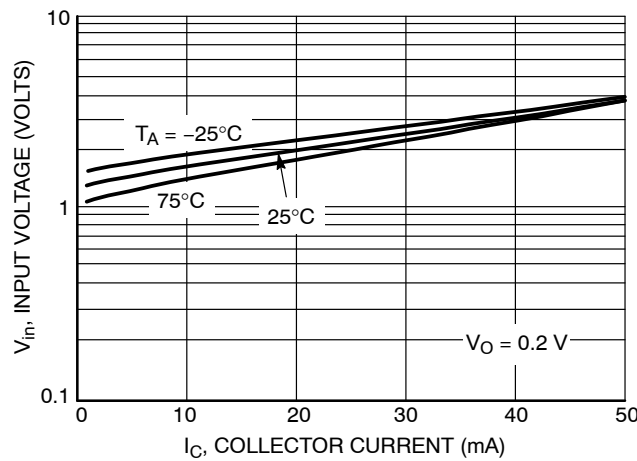


Figure 41. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5232DW1T1G, SMUN5232DW1T1G

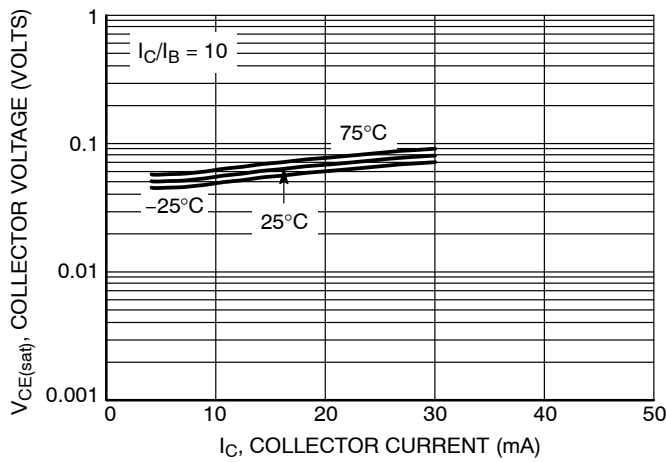


Figure 42. $V_{CE(sat)}$ versus I_C

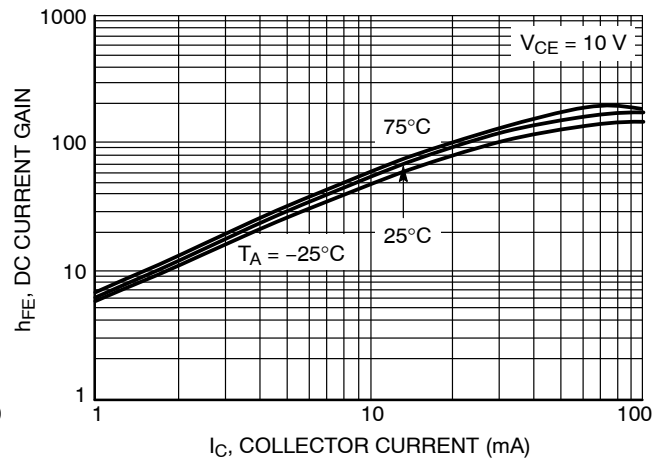


Figure 43. DC Current Gain

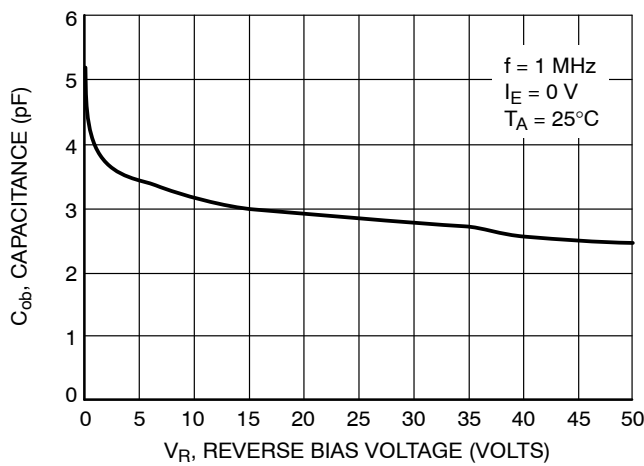


Figure 44. Output Capacitance

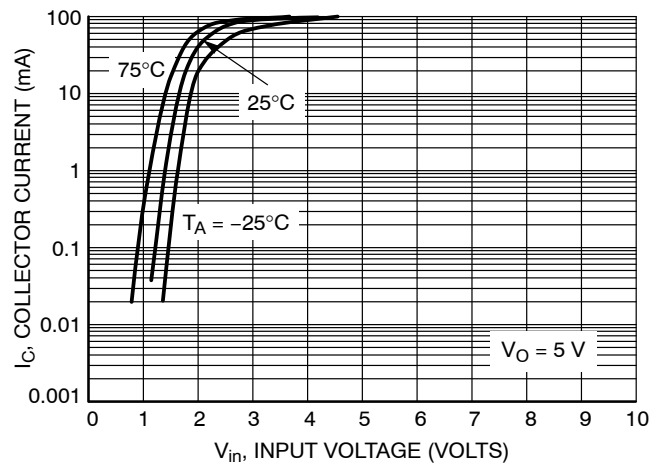


Figure 45. Output Current versus Input Voltage

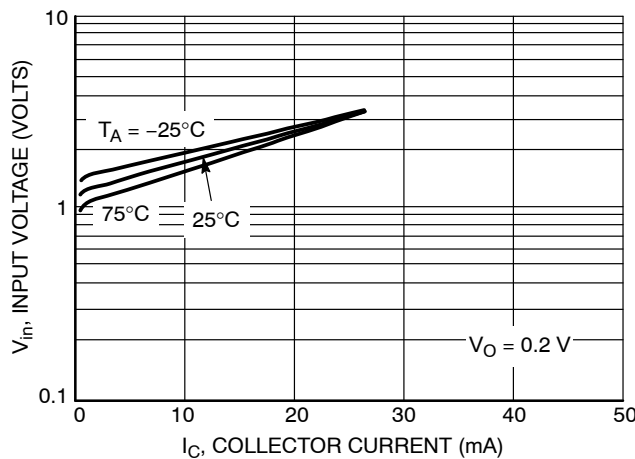


Figure 46. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5233DW1T1G, SMUN5233DW1T1G

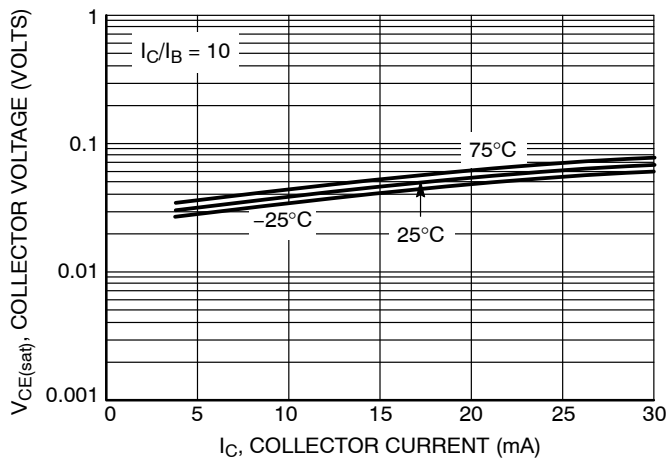


Figure 47. $V_{CE(sat)}$ versus I_C

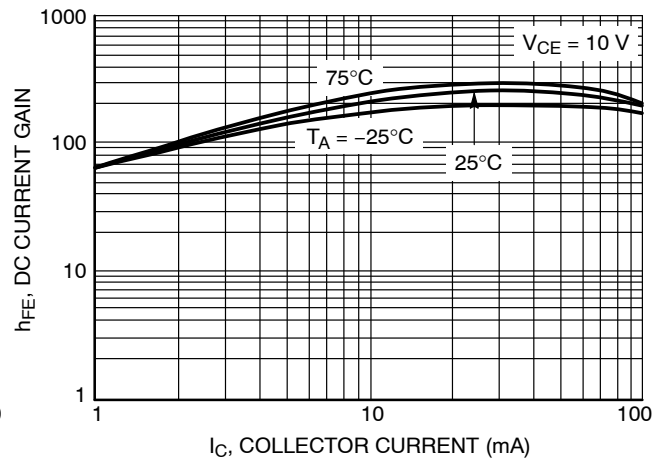


Figure 48. DC Current Gain

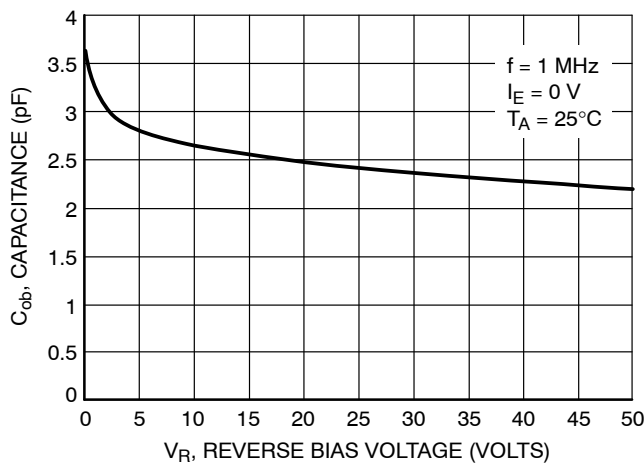


Figure 49. Output Capacitance

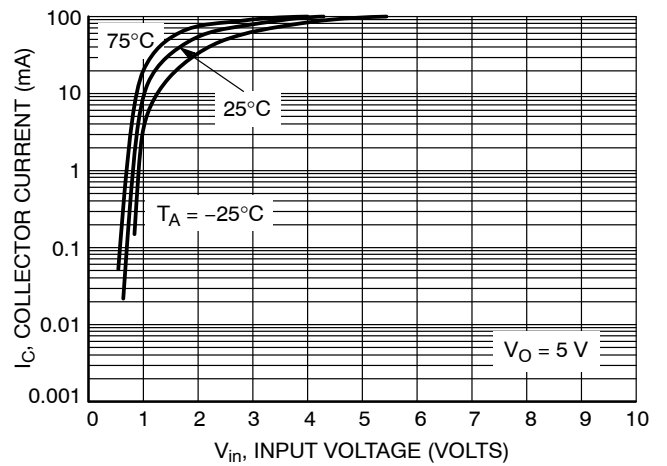


Figure 50. Output Current versus Input Voltage

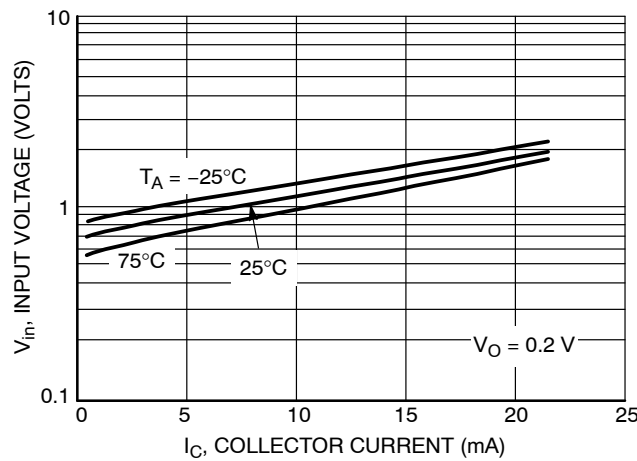


Figure 51. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5234DW1T1G

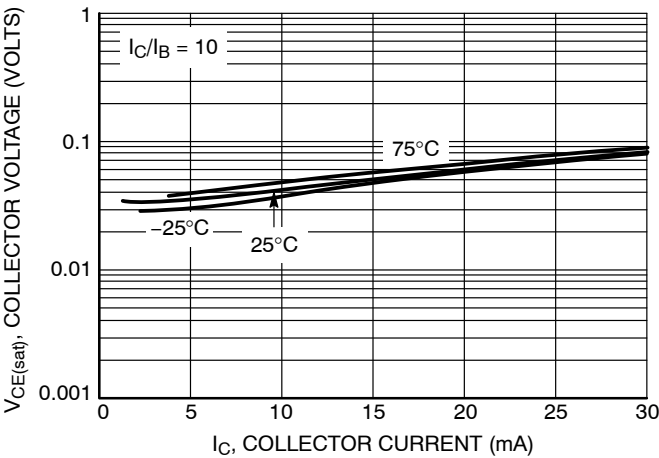


Figure 52. $V_{CE(sat)}$ versus I_C

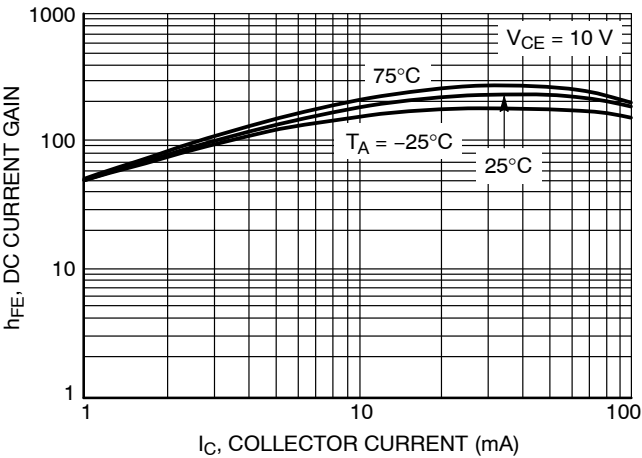


Figure 53. DC Current Gain

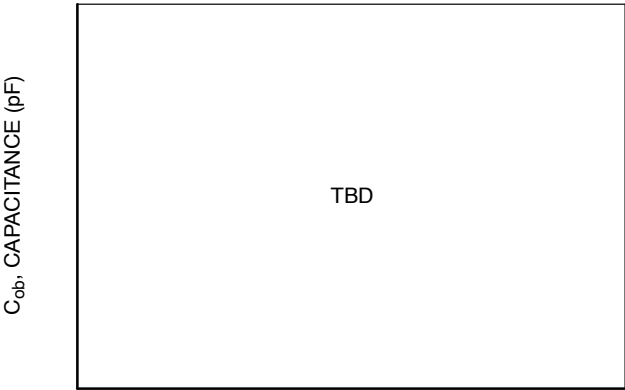


Figure 54. Output Capacitance

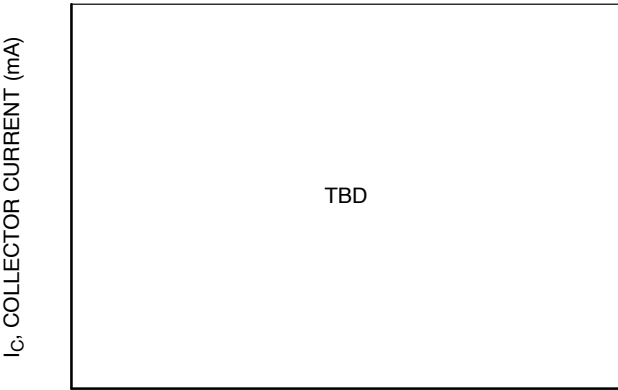


Figure 55. Output Current versus Input Voltage

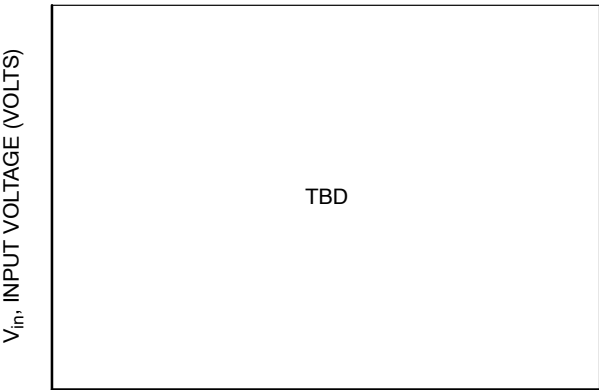


Figure 56. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5235DW1T1G, SMUN5235DW1T1G

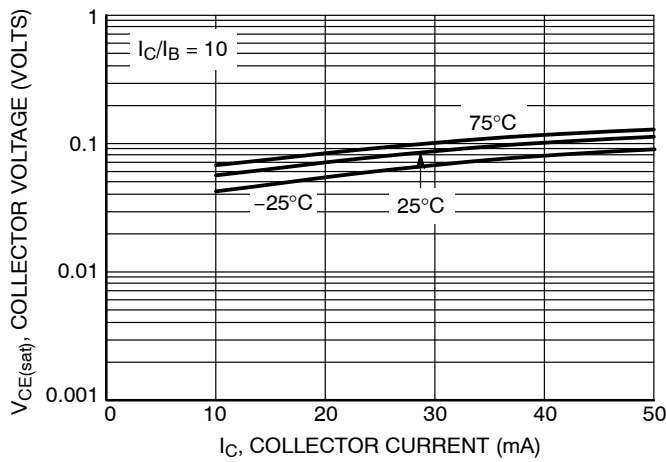


Figure 57. $V_{CE(sat)}$ versus I_C

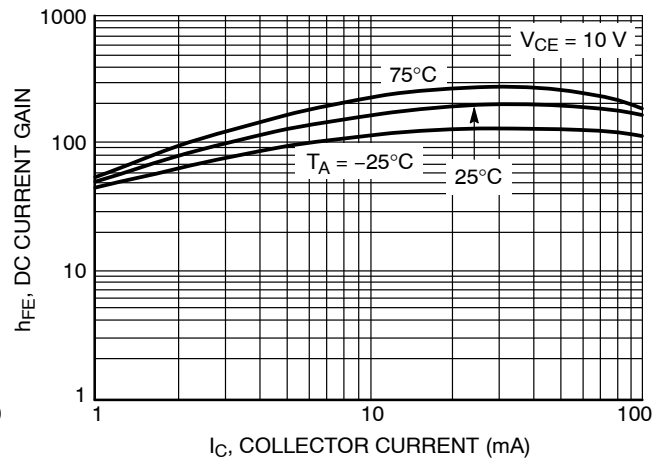


Figure 58. DC Current Gain

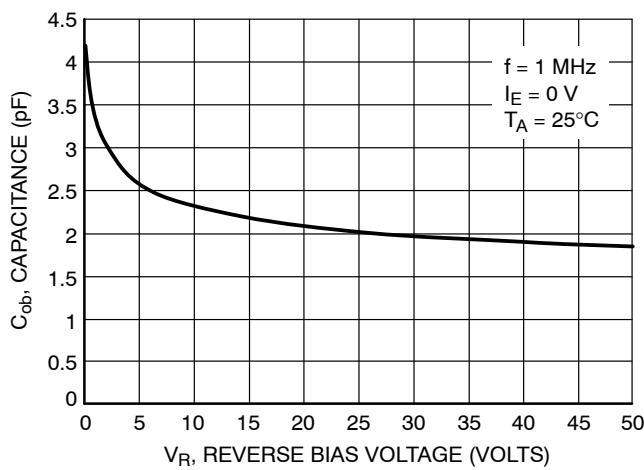


Figure 59. Output Capacitance

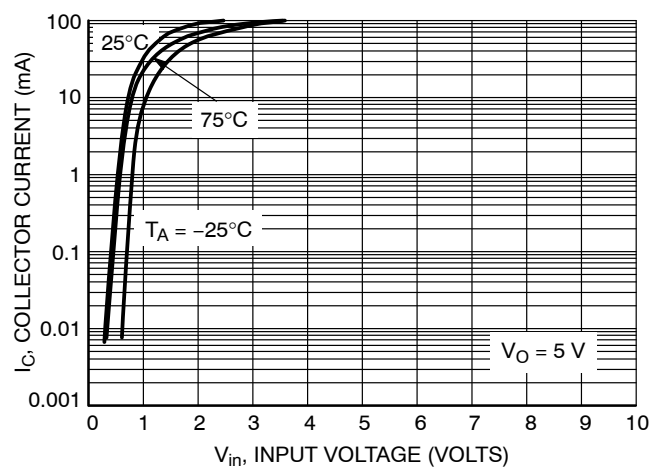


Figure 60. Output Current versus Input Voltage

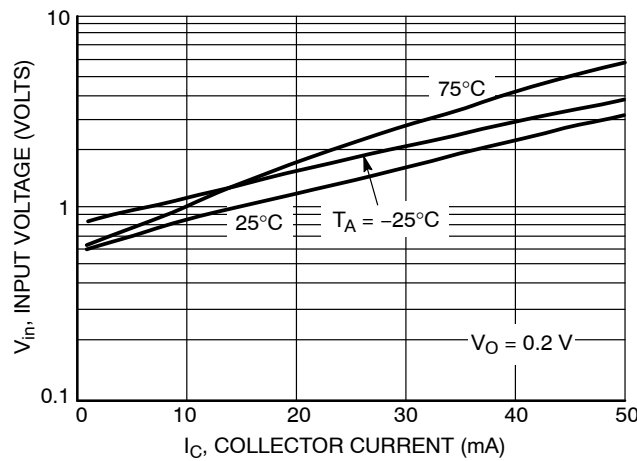


Figure 61. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5236DW1T1G

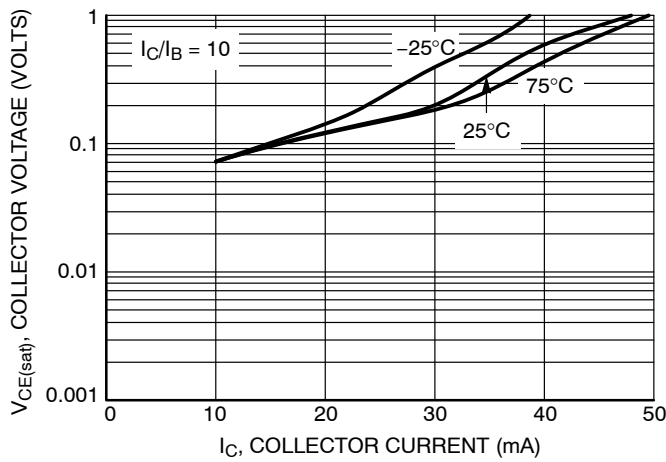


Figure 62. $V_{CE(sat)}$ versus I_C

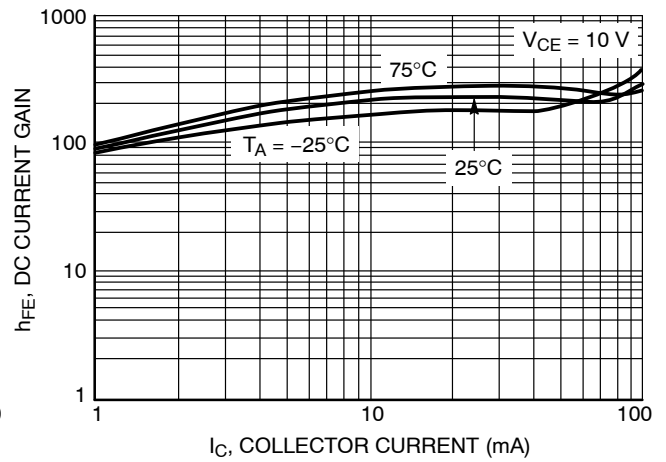


Figure 63. DC Current Gain

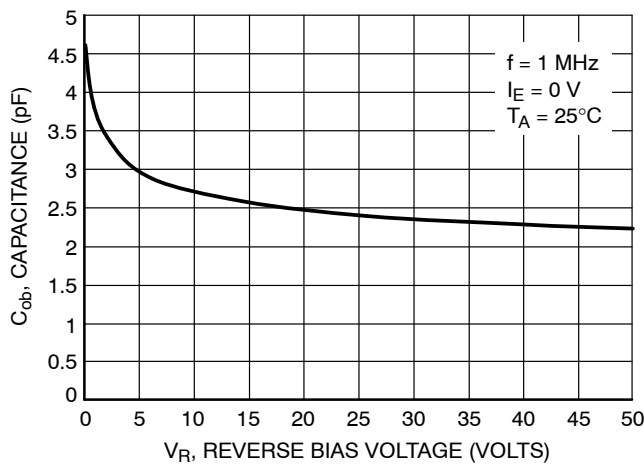


Figure 64. Output Capacitance

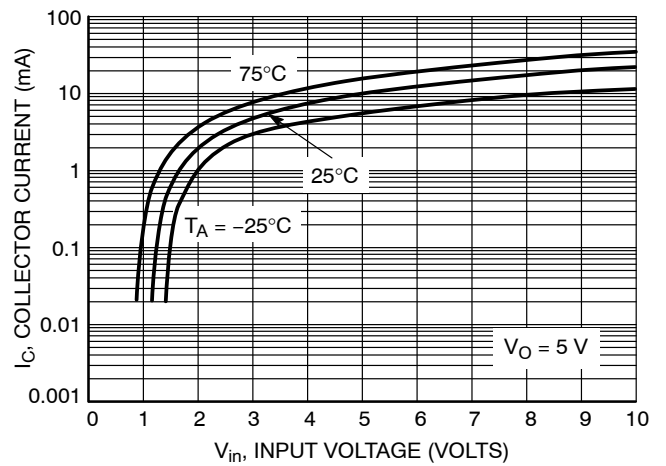


Figure 65. Output Current versus Input Voltage

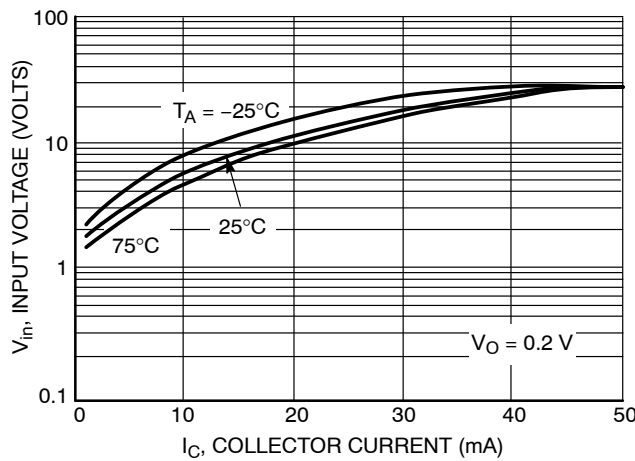


Figure 66. Input Voltage versus Output Current

MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

TYPICAL ELECTRICAL CHARACTERISTICS — MUN5237DW1T1G, SMUN5237DW1T1G

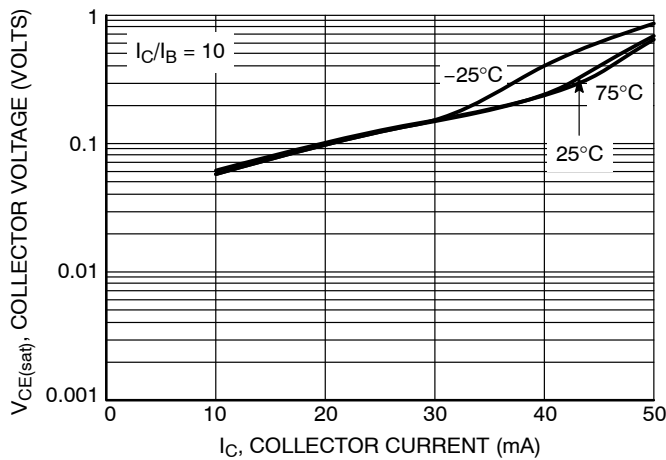


Figure 67. $V_{CE(sat)}$ versus I_C

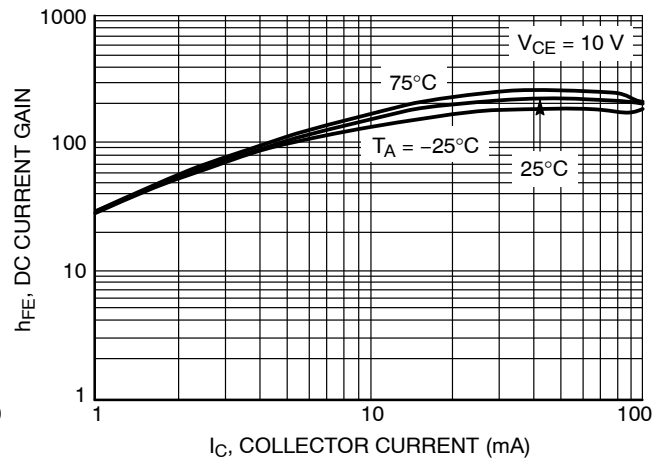


Figure 68. DC Current Gain

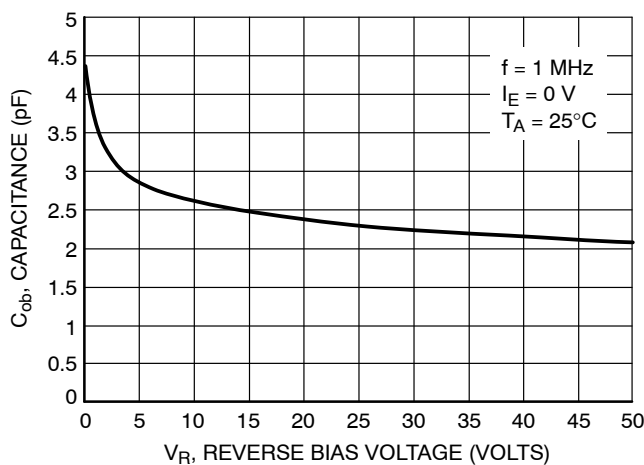


Figure 69. Output Capacitance

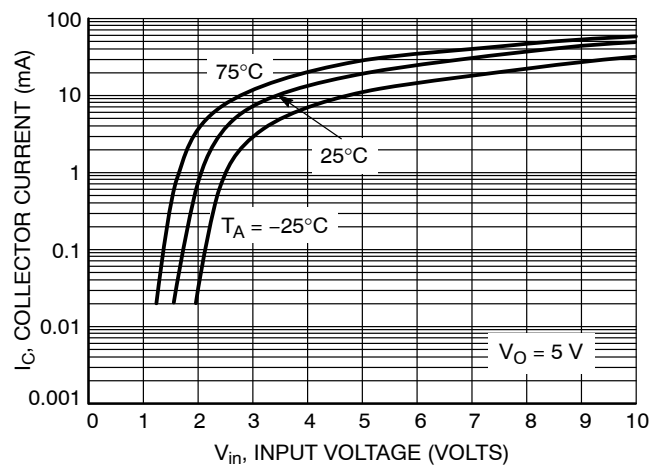


Figure 70. Output Current versus Input Voltage

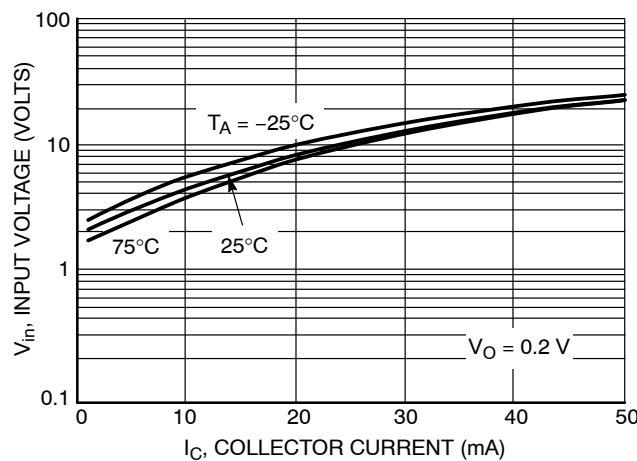


Figure 71. Input Voltage versus Output Current

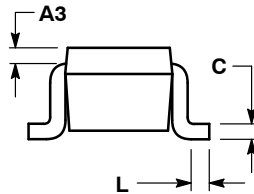
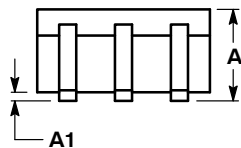
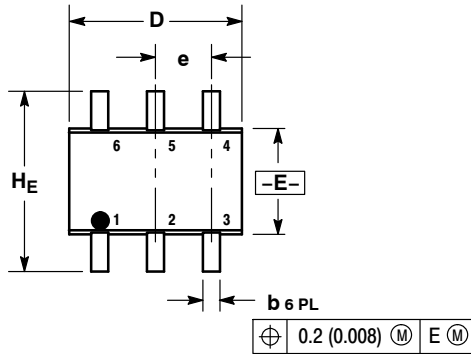
MUN5211DW1T1G, SMUN5211DW1T1G, NSVMUN5211DW1T1G Series

PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02

ISSUE W



NOTES:

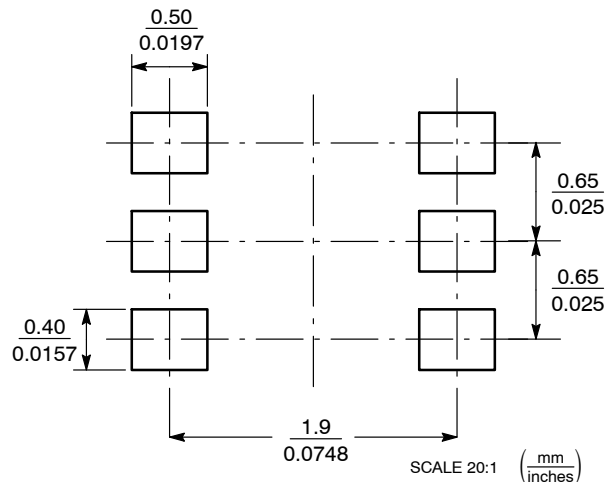
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.95	1.10	0.031	0.037	0.043
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012
C	0.10	0.14	0.25	0.004	0.005	0.010
D	1.80	2.00	2.20	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
He	2.00	2.10	2.20	0.078	0.082	0.086

STYLE 1:

- PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

SOLDERING FOOTPRINT*



SC-88/SC70-6/SOT-363

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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